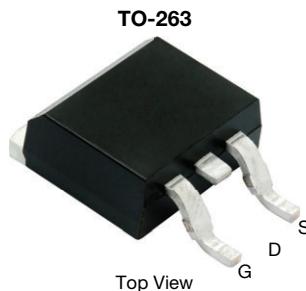
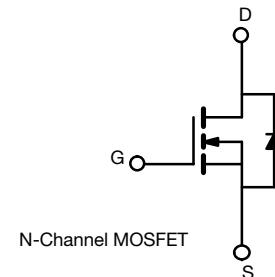


Automotive N-Channel 60 V (D-S) 175 °C MOSFET



FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- 100 % R_g and UIS tested
- AEC-Q101 qualified
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912



PRODUCT SUMMARY

V_{DS} (V)	60
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.0039
I_D (A)	100
Configuration	Single
Package	TO-263

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	60	V
Gate-source voltage	V_{GS}	± 20	
Continuous drain current	I_D	100	A
		80	
Continuous source current (diode conduction) ^a	I_S	100	A
Pulsed drain current ^b	I_{DM}	320	
Single pulse avalanche current	I_{AS}	50	mJ
Single pulse avalanche energy	E_{AS}	125	
Maximum power dissipation ^b	P_D	150	W
		50	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-ambient	R_{thJA}	40	°C/W
Junction-to-case (drain)	R_{thJC}	1	

Notes

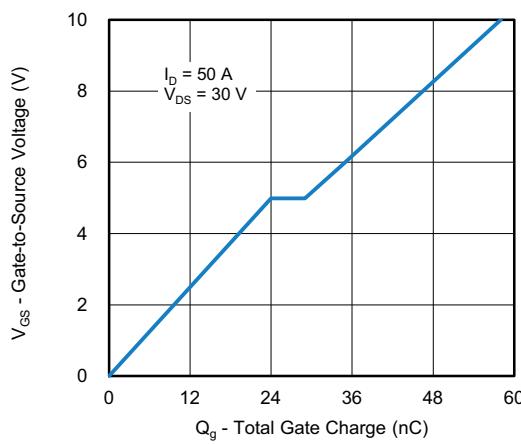
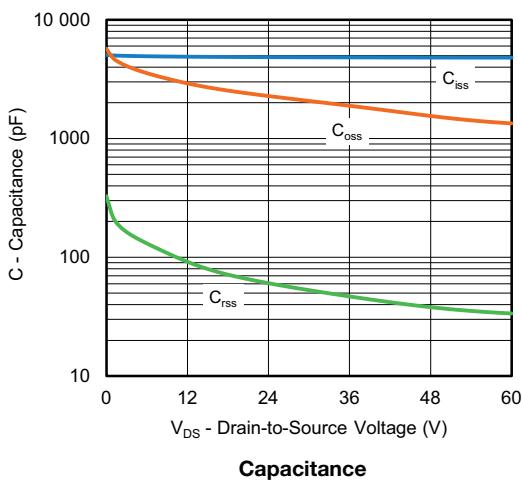
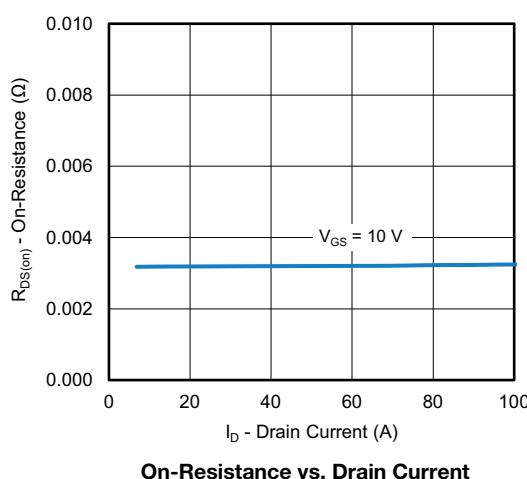
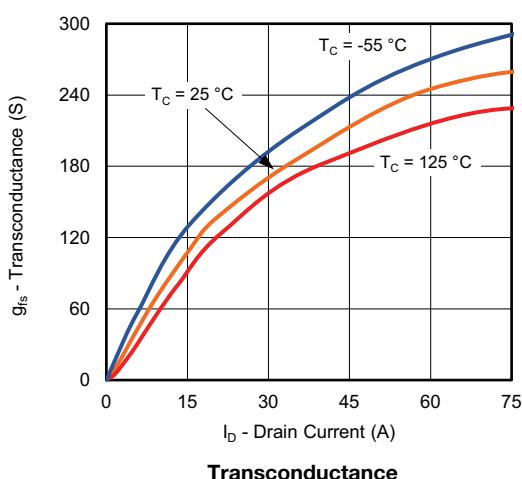
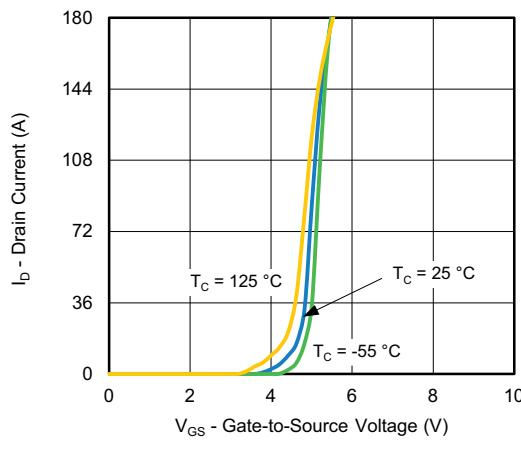
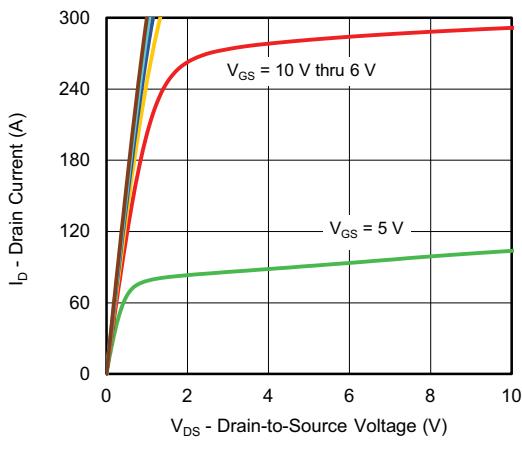
- Package limited
- Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)

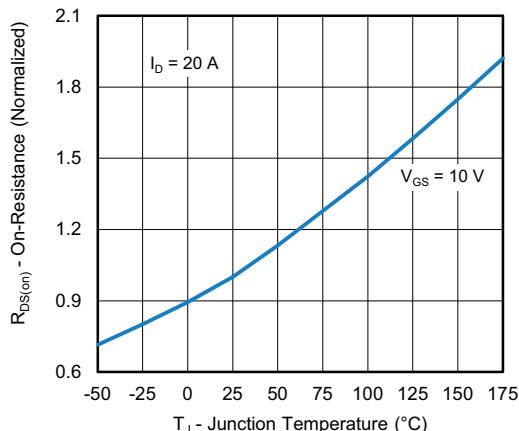
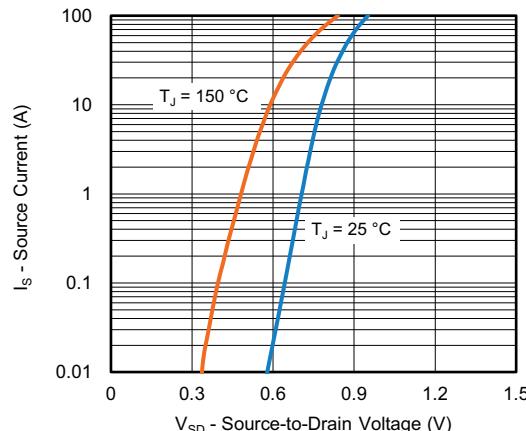
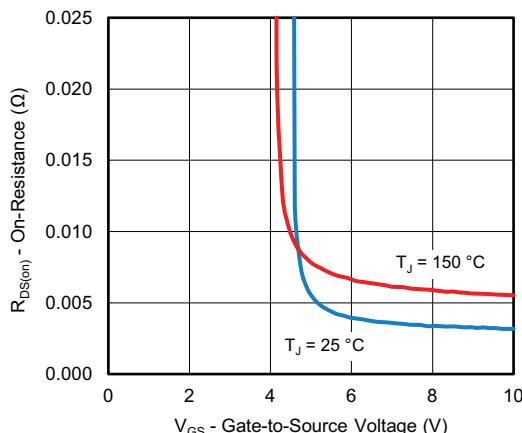
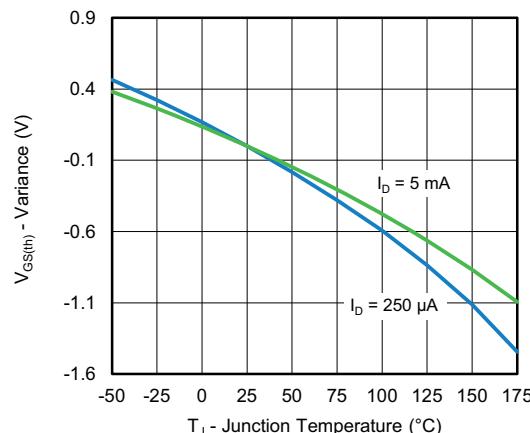
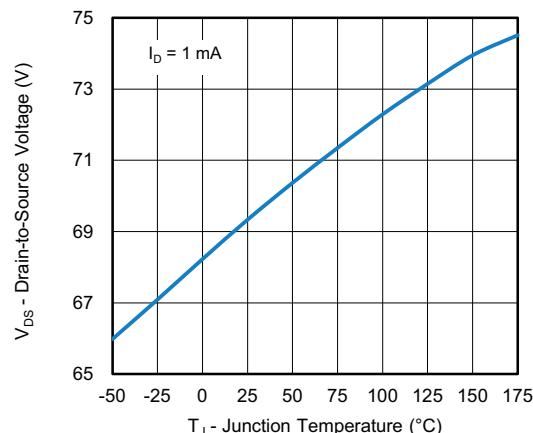
SPECIFICATIONS ($T_C = 25^\circ\text{C}$, unless otherwise noted)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$		60	-	-	V	
Gate-source threshold voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$		2.5	3.0	3.5		
Gate-source leakage	I_{GSS}	$V_{DS} = 0 \text{ V}$, $V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
Zero gate voltage drain current	I_{DSS}	$V_{GS} = 0 \text{ V}$	$V_{DS} = 60 \text{ V}$	-	-	1	μA	
		$V_{GS} = 0 \text{ V}$	$V_{DS} = 60 \text{ V}$, $T_J = 125^\circ\text{C}$	-	-	50		
		$V_{GS} = 0 \text{ V}$	$V_{DS} = 60 \text{ V}$, $T_J = 175^\circ\text{C}$	-	-	300	μA	
On-state drain current ^a	$I_{D(\text{on})}$	$V_{GS} = 10 \text{ V}$	$V_{DS} \geq 5 \text{ V}$	100	-	-	A	
Drain-source on-state resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}$	$I_D = 20 \text{ A}$	-	0.0032	0.0039	Ω	
		$V_{GS} = 10 \text{ V}$	$I_D = 20 \text{ A}$, $T_J = 125^\circ\text{C}$	-	-	0.0062		
		$V_{GS} = 10 \text{ V}$	$I_D = 20 \text{ A}$, $T_J = 175^\circ\text{C}$	-	-	0.0075		
Forward transconductance ^b	g_{fs}	$V_{DS} = 15 \text{ V}$, $I_D = 20 \text{ A}$		-	135	-	S	
Dynamic ^b								
Input capacitance	C_{iss}	$V_{GS} = 0 \text{ V}$	$V_{DS} = 25 \text{ V}$, $f = 1 \text{ MHz}$	-	4841	6600	pF	
Output capacitance	C_{oss}			-	2243	3100		
Reverse transfer capacitance	C_{rss}			-	60	85		
Total gate charge ^c	Q_g	$V_{GS} = 10 \text{ V}$	$V_{DS} = 30 \text{ V}$, $I_D = 50 \text{ A}$	-	58	90	nC	
Gate-source charge ^c	Q_{gs}			-	24	-		
Gate-drain charge ^c	Q_{gd}			-	5	-		
Gate resistance	R_g	$f = 1 \text{ MHz}$		0.6	1.26	1.9	Ω	
Turn-on delay time ^c	$t_{d(\text{on})}$	$V_{DD} = 30 \text{ V}$, $R_L = 0.6 \Omega$ $I_D \equiv 50 \text{ A}$, $V_{GEN} = 10 \text{ V}$, $R_g = 1 \Omega$		-	19	30	ns	
Rise time ^c	t_r			-	10	20		
Turn-off delay time ^c	$t_{d(\text{off})}$			-	30	50		
Fall time ^c	t_f			-	8	15		
Source-Drain Diode Ratings and Characteristics ^b								
Pulsed current ^a	I_{SM}			-	-	320	A	
Forward voltage	V_{SD}	$I_F = 25 \text{ A}$, $V_{GS} = 0 \text{ V}$		-	0.83	1.5	V	
Body diode reverse recovery time	t_{rr}	$I_F = 30 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$		-	50	100	ns	
Body diode reverse recovery charge	Q_{rr}			-	55	110	nC	
Reverse recovery fall time	t_a			-	24	-	ns	
Reverse recovery rise time	t_b			-	26	-		
Body diode peak reverse recovery current	$I_{RM(\text{REC})}$			-	-1.92	-	A	

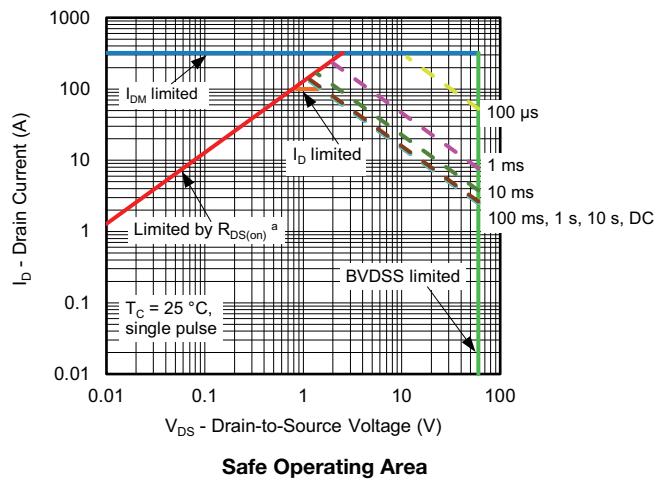
Notes

- a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

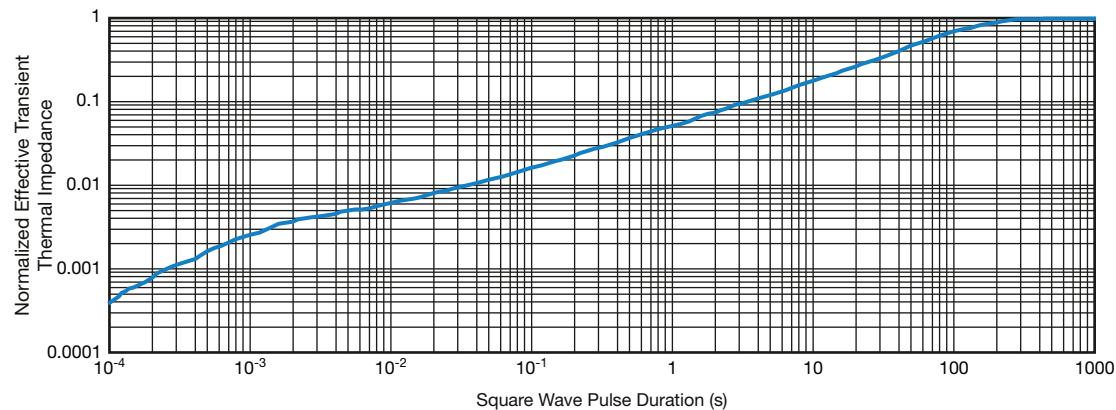
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

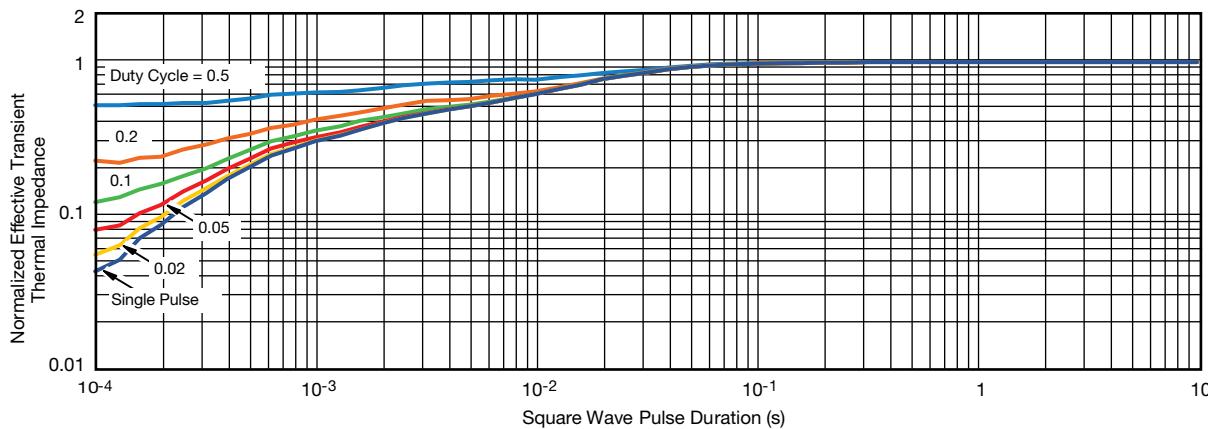
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)


TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

On-Resistance vs. Junction Temperature

Source Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Drain Source Breakdown vs. Junction Temperature

THERMAL RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Note

a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified


Normalized Thermal Transient Impedance, Junction-to-Ambient

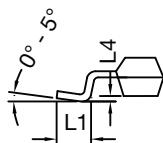
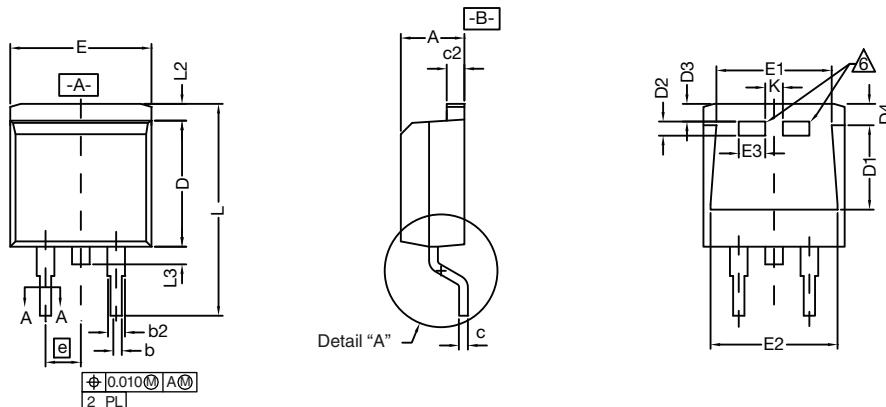
THERMAL RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Case
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25°C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25°C)

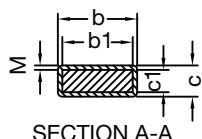
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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TO-263 (D²PAK): 3-LEAD



DETAIL A (ROTATED 90°)

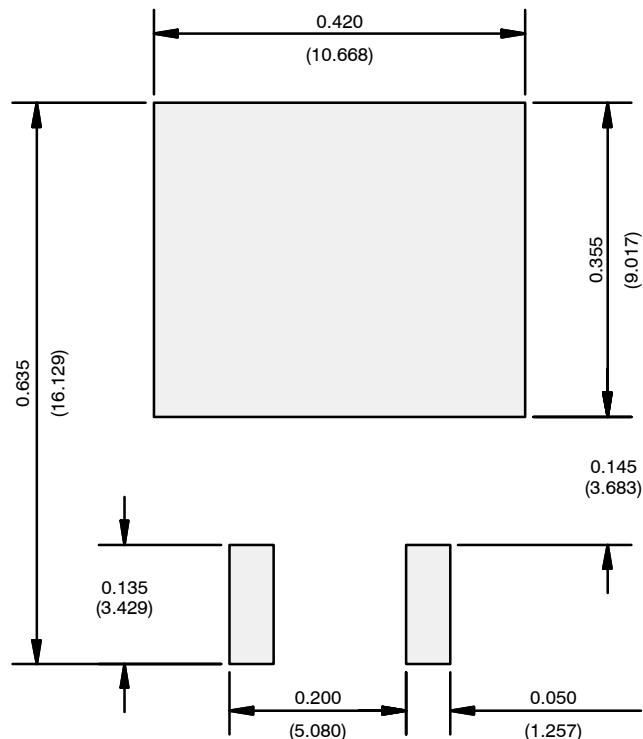


SECTION A-A

Notes

1. Plane B includes maximum features of heat sink tab and plastic.
 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
 3. Pin-to-pin coplanarity max. 4 mils.
 4. *: Thin lead is for SUB, SYB.
Thick lead is for SUM, SYM, SQM.
 5. Use inches as the primary measurement.
- This feature is for thick lead.

DIM.	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	0.160	0.190	4.064	4.826	
b	0.020	0.039	0.508	0.990	
b1	0.020	0.035	0.508	0.889	
b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2		0.045	0.055	1.143	1.397
D	0.340	0.380	8.636	9.652	
D1	0.220	0.240	5.588	6.096	
D2	0.038	0.042	0.965	1.067	
D3	0.045	0.055	1.143	1.397	
D4	0.044	0.052	1.118	1.321	
E	0.380	0.410	9.652	10.414	
E1	0.245	-	6.223	-	
E2	0.355	0.375	9.017	9.525	
E3	0.072	0.078	1.829	1.981	
e	0.100 BSC		2.54 BSC		
K	0.045	0.055	1.143	1.397	
L	0.575	0.625	14.605	15.875	
L1	0.090	0.110	2.286	2.794	
L2	0.040	0.055	1.016	1.397	
L3	0.050	0.070	1.270	1.778	
L4	0.010 BSC		0.254 BSC		
M	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13					
DWG: 5843					

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead

Recommended Minimum Pads
Dimensions in Inches/(mm)

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- Поставка более 17-ти миллионов наименований электронных компонентов;
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- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



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